

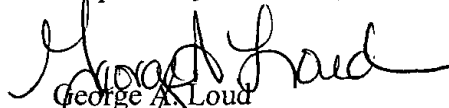
Please add the following new claims:

--13. A semiconductor device manufacturing method according to claim 7, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

14. A semiconductor device manufacturing method according to claim 8, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

15. A semiconductor device manufacturing method according to claim 11, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.--

Respectfully submitted,


George A. Loud
Reg. No. 23,814

Dated: March 15, 2001

LORUSSO & LOUD
3137 Mount Vernon Avenue
Alexandria, VA 22305
(703) 739-9393

12. (Amended) A semiconductor device manufacturing method according to claim 6 [any one of claims 6, 7, 8, and 11], wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

0908015-031501
"FILED" 0908015